N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.0095 at V_{GS} = 10 V	13
	0.0105 at V_{GS} = 4.5 V	12

SCHOTTKY PRODUCT SUMMARY		
V_{DS} (V)	V_{SD} (V) Diode Forward Voltage	I_F (A)
30	0.53 V at 3.0 A	3.0

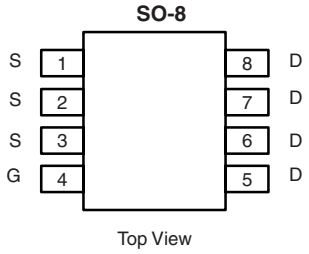
FEATURES

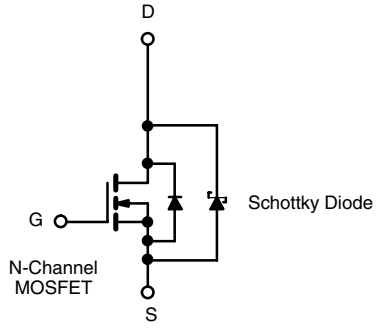
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- LITTLE FOOT® *Plus* Schottky
- Shoot-Thru-Free
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- DC/DC Converters Optimized for "Low-Side" Synchronous Rectifier Operation





Ordering Information: Si4736DY-T1-E3 (Lead (Pb)-free)
Si4736DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	13	9	A
	T_A = 70 °C		10	7	
Pulsed Drain Current		I_{DM}	50		
Continuous Source Current (Diode Conduction)[a]		I_S	5	3.0	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	3.1	1.40	W
	T_A = 70 °C		2.0	0.90	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typ.**	**Max.**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	33	40	°C/W
	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

Notes:
a. Surface Mounted on 1" x 1" FR4 board.

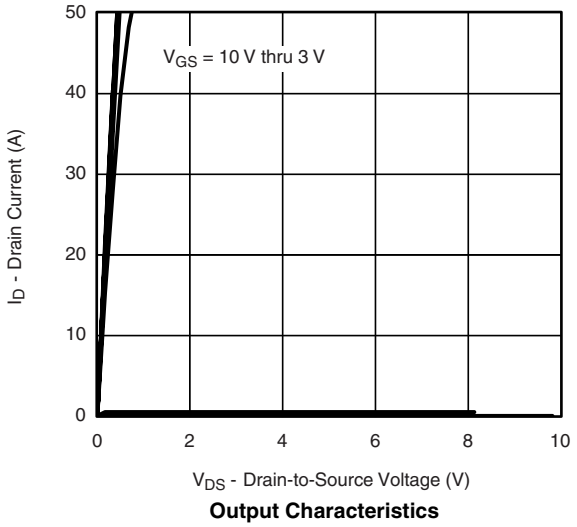
This data sheet contains preliminary specifications that are subject to change.

MOSFET SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.8	1.35	1.9	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V		0.007	0.100	mA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 100 °C		1.5	10	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 125 °C		6.5	20	
On-State Drain Current[b]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	20			A
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 13 A		0.0070	0.0095	Ω
		V_{GS} = 4.5 V, I_D = 12 A		0.0083	0.0105	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 13 A		56		S
Diode Forward Voltage[b]	V_{SD}	I_S = 3.0 A, V_{GS} = 0 V		0.495	0.53	V
		I_S = 3.0 A, V_{GS} = 0 V, T_J = 125 °C		0.430	0.47	
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 13 A		37	55	nC
Gate-Source Charge	Q_{gs}			10		
Gate-Drain Charge	Q_{gd}			8.8		
Gate Resistance	R_g			0.8		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω $I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		17	26	ns
Rise Time	t_r			14	21	
Turn-Off Delay Time	$t_{d(off)}$			102	155	
Fall Time	t_f			26	40	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 3.0 A, dI/dt = 100 A/µs		42	65	

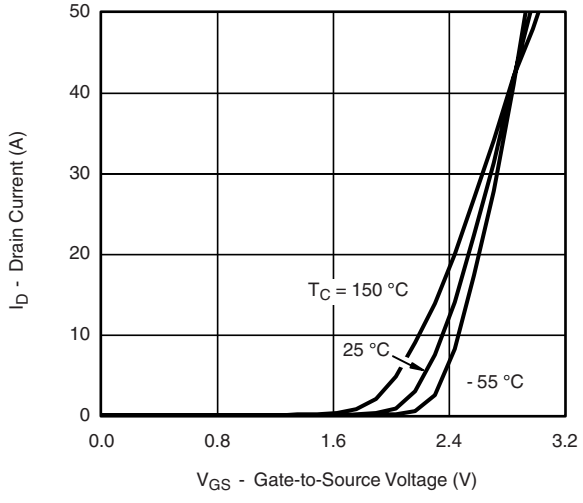
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

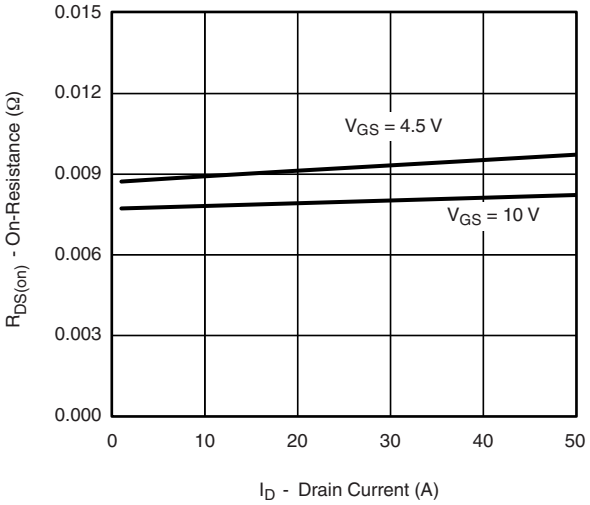


Output Characteristics

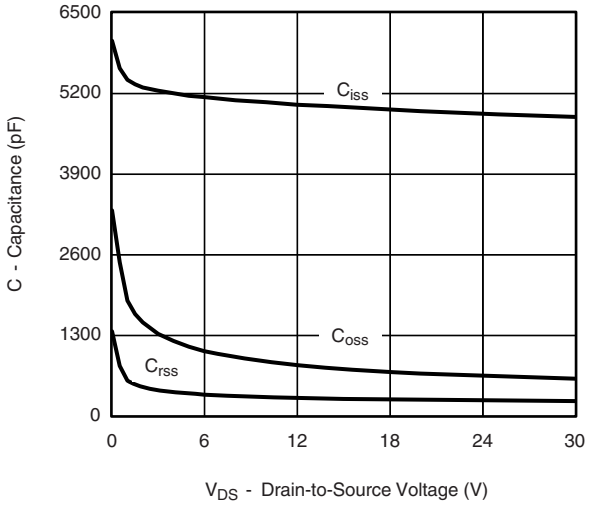


Transfer Characteristics

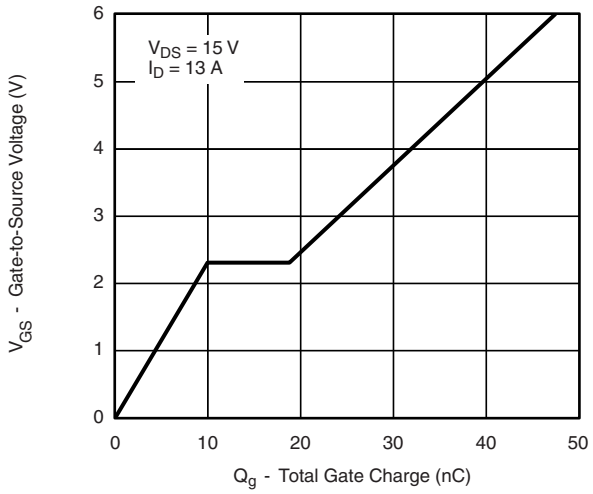
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



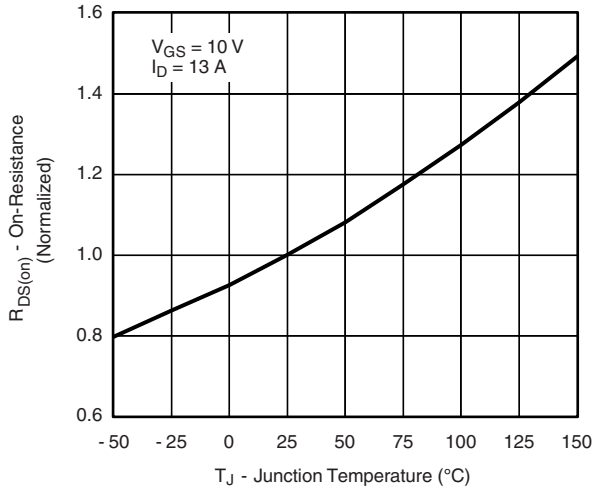
On-Resistance vs. Drain Current



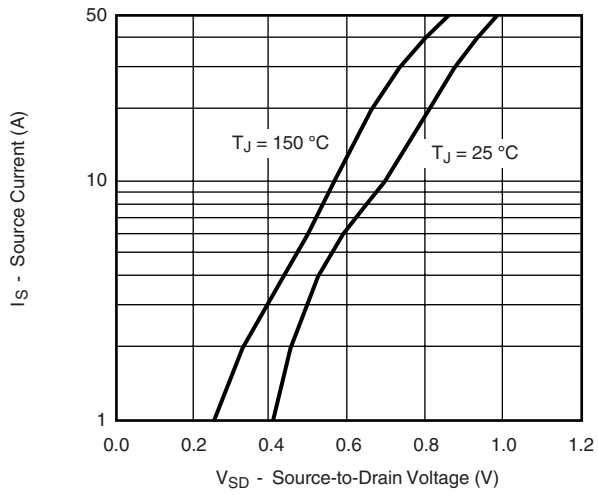
Capacitance



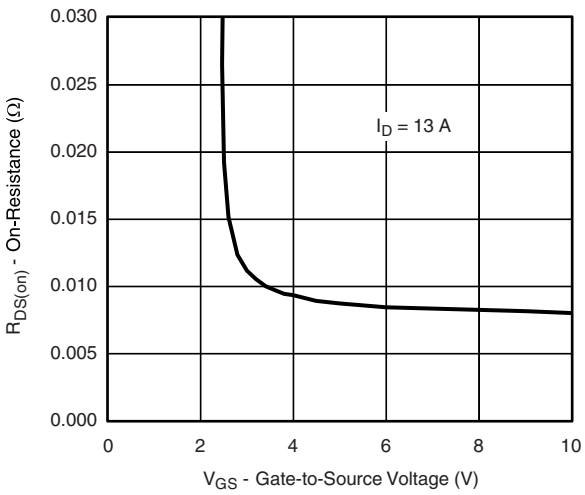
Gate Charge



On-Resistance vs. Junction Temperature

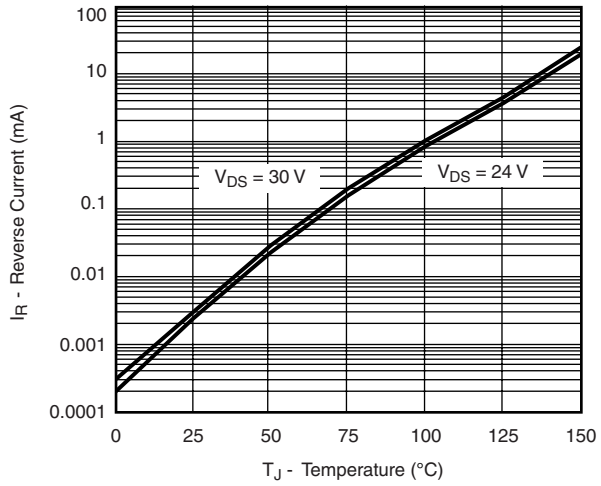


Source-Drain Diode Forward Voltage

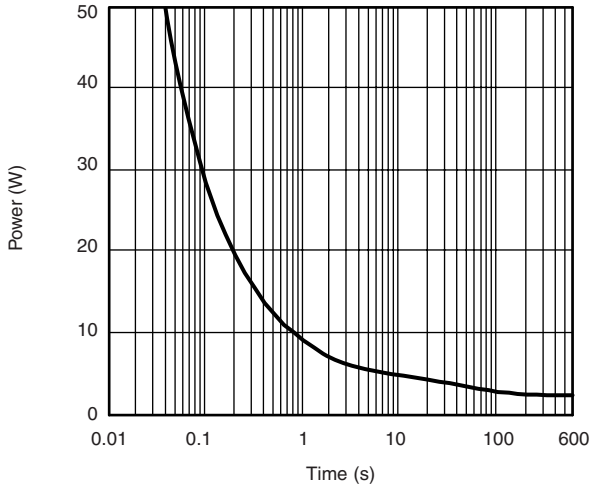


On-Resistance vs. Gate-to-Source Voltage

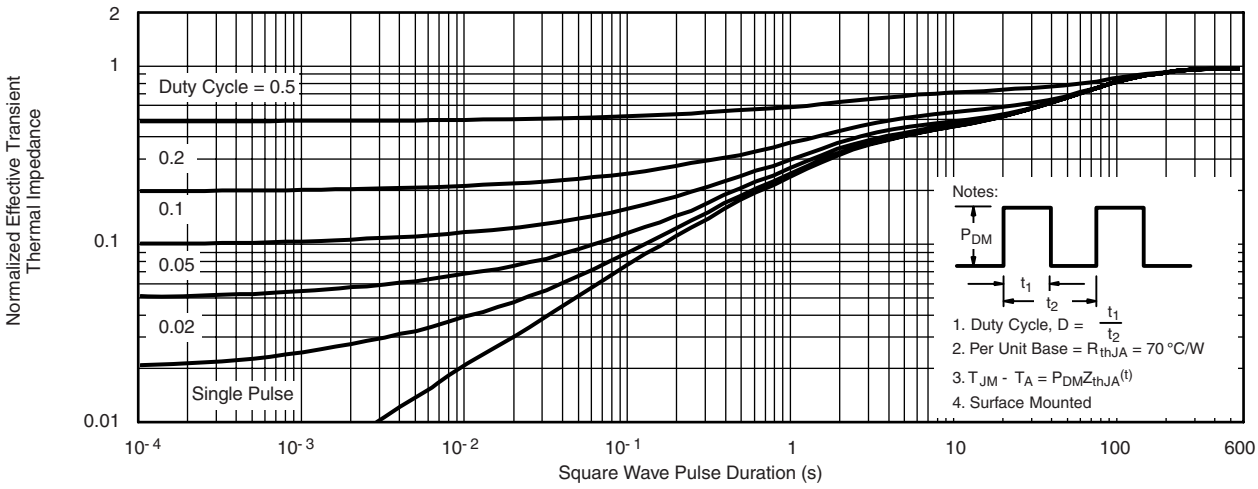
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



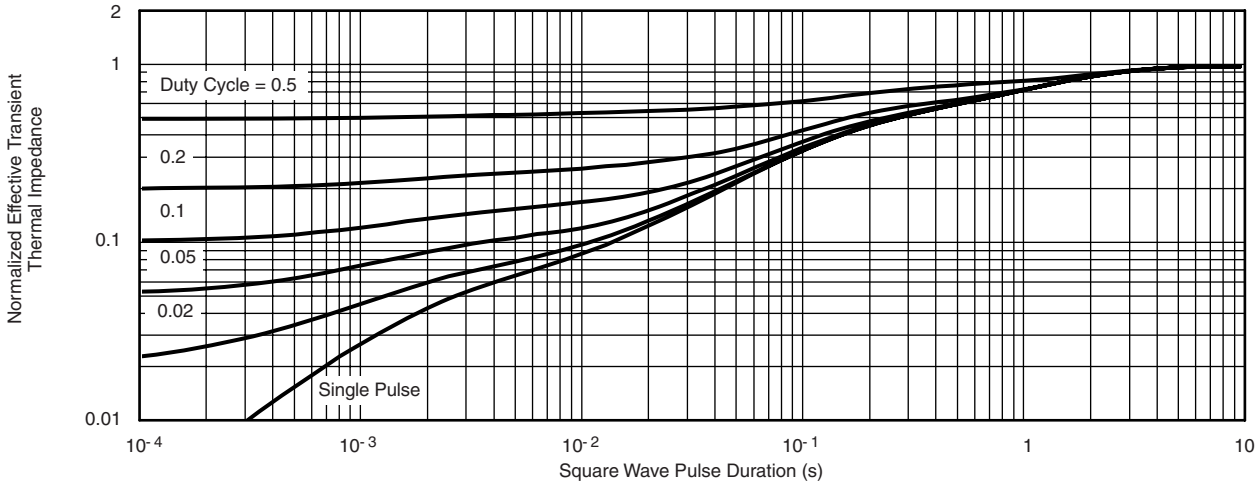
Reverse Current vs. Junction Temperature



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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